## Platon A Karaseov

List of Publications by Year in descending order

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#	Article	IF	CITATIONS
1	Effect of the density of collision cascades on ion implantation damage in ZnO. Journal of Applied Physics, 2007, 102, 083547.	2.5	37
2	Energy spike effects in ion-bombarded GaN. Journal Physics D: Applied Physics, 2009, 42, 085309.	2.8	29
3	Structural damage in ZnO bombarded by heavy ions. Vacuum, 2010, 84, 1058-1061.	3.5	22
4	Density of displacement cascades for cluster ions: An algorithm of calculation and the influence on damage formation in ZnO and GaN. Semiconductors, 2009, 43, 691-700.	0.5	18
5	Atomistic simulation of damage production by atomic and molecular ion irradiation in GaN. Journal of Applied Physics, 2012, 112, .	2.5	18
6	Model for radiation damage buildup in GaN. Nuclear Instruments & Methods in Physics Research B, 2012, 277, 80-83.	1.4	16
7	In-situ transport and microstructural evolution in GaN Schottky diodes and epilayers exposed to swift heavy ion irradiation. Journal of Applied Physics, 2018, 123, 161539.	2.5	14
8	Influence of ion irradiation on internal residual stress in DLC films. Nuclear Instruments & Methods in Physics Research B, 2010, 268, 3107-3110.	1.4	13
9	Damage formation in Si under irradiation with PF n + ions of different energies. Semiconductors, 2013, 47, 242-246.	0.5	12
10	Effect of ion bombardment on the phase composition and mechanical properties of diamond-like carbon films. Journal of Surface Investigation, 2014, 8, 45-49.	0.5	12
11	The mechanism of charge carrier generation at the TiO2—n-Si heterojunction activated by gold nanoparticles. Semiconductor Science and Technology, 2018, 33, 075014.	2.0	12
12	Defect clustering in irradiation of GaN by single and molecular ions. Vacuum, 2014, 105, 88-90.	3.5	11
13	A model of electrical isolation in GaN and ZnO bombarded with light ions. Semiconductors, 2004, 38, 1179-1186.	0.5	10
14	Effect of collision cascade density on radiation damage in SiC. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 1247-1250.	1.4	10
15	Residual stress in diamond-like carbon films: Role of growth conditions and ion irradiation. Journal of Surface Investigation, 2010, 4, 241-244.	0.5	9
16	Molecular effect on surface topography of GaN bombarded with PF4 ions. Vacuum, 2012, 86, 1638-1641.	3.5	9
17	Effects of defect clustering on optical properties of GaN by single and molecular ion irradiation. Journal of Applied Physics, 2013, 114, .	2.5	9
18	Effects of the density of collision cascades: Separating contributions from dynamic annealing and energy spikes. Nuclear Instruments & Methods in Physics Research B, 2009, 267, 2701-2704.	1.4	8

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19	Nonlinear optical effect upon the irradiation of GaN with cluster ions. Semiconductors, 2014, 48, 446-450.	0.5	8
20	Experimental study and MD simulation of damage formation in GaN under atomic and molecular ion irradiation. Vacuum, 2016, 129, 166-169.	3.5	8
21	Effect of an increase in the density of collision cascades on the efficiency of the generation of primary displacements during the ion bombardment of Si. Semiconductors, 2016, 50, 989-995.	0.5	7
22	Do Chemical Effects Affect the Accumulation of Structural Damage during the Implantation of Fluorine Ions into GaN?. Semiconductors, 2019, 53, 1415-1418.	0.5	7
23	Formation of wear-resistant graphite/diamond-like carbon nanocomposite coatings on Ti using accelerated C60-ions. Surface and Coatings Technology, 2021, 424, 127670.	4.8	6
24	Dislocation-related photoluminescence in silicon implanted with fluorine ions. Technical Physics Letters, 2017, 43, 50-52.	0.7	5
25	The effect of diborane additive on the plasma-chemical properties of deposited carbon films. Technical Physics Letters, 2017, 43, 81-84.	0.7	5
26	The formation of radiation damage in GaN during successive bombardment by light ions of various energies. Vacuum, 2020, 173, 109149.	3.5	5
27	Formation of Au Nanoparticles and Features of Etching of a Si Substrate under Irradiation with Atomic and Molecular lons. Semiconductors, 2020, 54, 137-143.	0.5	5
28	Electrooptical Properties of TiO2 Doped with Gold Nanoparticles. Semiconductors, 2020, 54, 1885-1888.	0.5	5
29	Formation of Functional Conductive Carbon Coating on Si by C60 Ion Beam. Springer Proceedings in Physics, 2021, , 131-139.	0.2	5
30	Furthering the understanding of ion-irradiation-induced electrical isolation in wide band-gap semiconductors. Nuclear Instruments & Methods in Physics Research B, 2006, 243, 79-82.	1.4	4
31	Swift heavy ion irradiation of metal containing tetrahedral amorphous carbon films. Nuclear Instruments & Methods in Physics Research B, 2016, 379, 162-166.	1.4	4
32	Single and molecular ion irradiation-induced effects in GaN: experiment and cumulative MD simulations. Journal Physics D: Applied Physics, 2017, 50, 505110.	2.8	4
33	Substrate modification influence on properties of nanocomposite based on TiO <sub>2</sub> and gold nanoparticles. Journal of Physics: Conference Series, 2019, 1236, 012025.	0.4	4
34	Effect of monatomic and molecular ion irradiation on time resolved photoluminescence decay in GaN. Nuclear Instruments & Methods in Physics Research B, 2019, 458, 164-168.	1.4	4
35	Effect of collision cascade density on swelling and surface topography of GaN. Nuclear Instruments & Methods in Physics Research B, 2013, 315, 257-260.	1.4	3
36	Formation of Radiation Defects by Proton Braking in Lightly Doped n- and p-SiC Layers. Semiconductors, 2018, 52, 310-315.	0.5	3

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37	Influence of ion bombardment on residual stresses in diamond-like carbon films. Journal of Surface Investigation, 2009, 3, 235-238.	0.5	2
38	Ranges of 10–350 keV H and H 2 ions in (1 1 1) diamond. Nuclear Instruments & Methods in Physics Research B, 2017, 406, 634-637.	1.4	2
39	Radiation tolerance of GaN: the balance between radiation-stimulated defect annealing and defect stabilization by implanted atoms. Journal Physics D: Applied Physics, 2022, 55, 175103.	2.8	2
40	Modification of properties of metal containing carbon films by swift heavy ion irradiation. , 2014, , .		1
41	Optical properties of plasmonic metal nanoparticles on GaN surface. Journal of Physics: Conference Series, 2021, 2086, 012127.	0.4	1
42	Computer simulation of electron diffraction by soft crystal potential. , 1998, 3345, 118.		0
43	Effect of growth conditions on carbon film properties. , 2014, , .		0
44	International Conference "Emerging Trends in Applied and Computational Physics 2019―(ETACP-2019). Journal of Physics: Conference Series, 2019, 1236, 011001.	0.4	0
45	Breakdown Strength of Polypropylene Films Demetallized by High-Power Surface Discharge. , 2021, , .		Ο
46	Impact of Chemical Effects on Topography and Thickness of Modified GaN Surface Layers Bombarded by F and Ne Ions. Springer Proceedings in Physics, 2021, , 151-157.	0.2	0
47	Study of Low Energy Ion Beam-Assisted Mixing in Al/Sb Bilayer. , 2021, , .		0